

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## S8550-MS

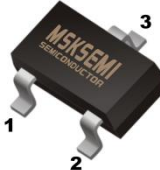

Product specification

TRANSISTOR (PNP)

**FEATURES**

- Complimentary to S8050-MS
- Collector current:  $I_C=0.5A$

**Reference News**

PACKAGE OUTLINE	MARKING
 <p>1. BASE 2. EMITTER 3. COLLECTOR</p>	
SOT-23	

**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-25	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current -Continuous	-0.5	A
$P_C$	Collector Dissipation	0.3	W
$T_j$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature	-55-150	°C

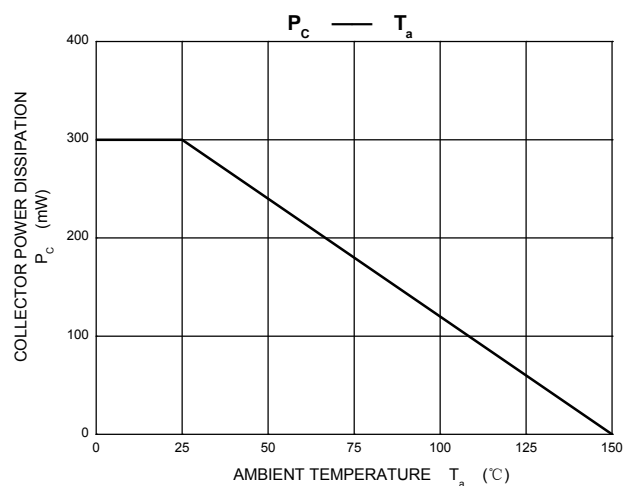
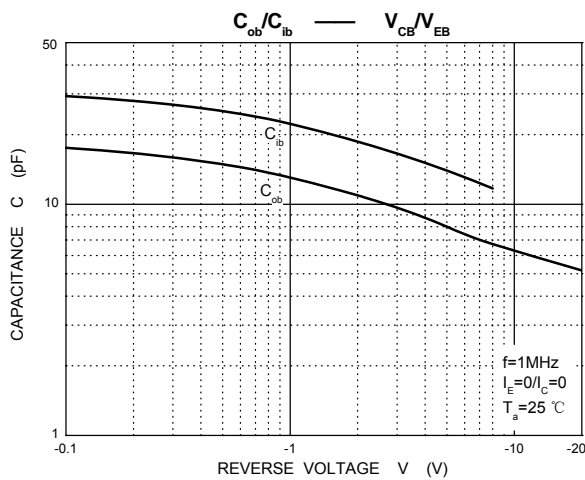
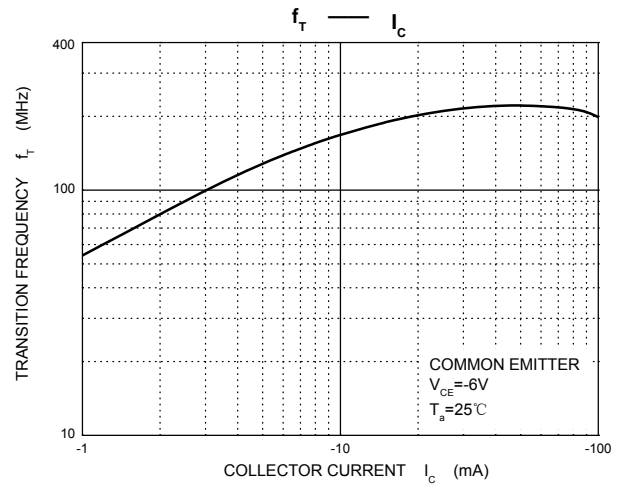
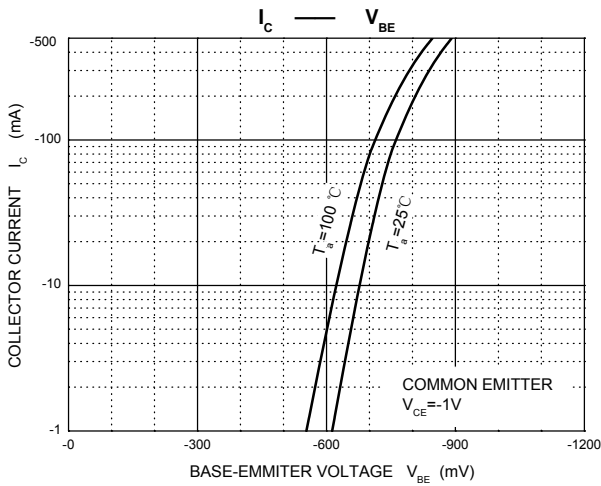
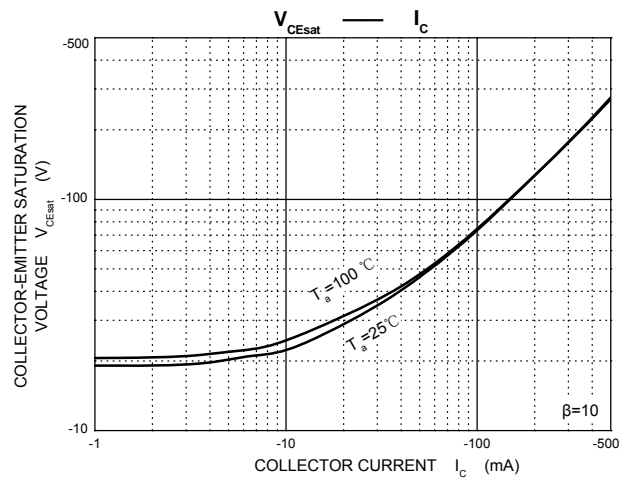
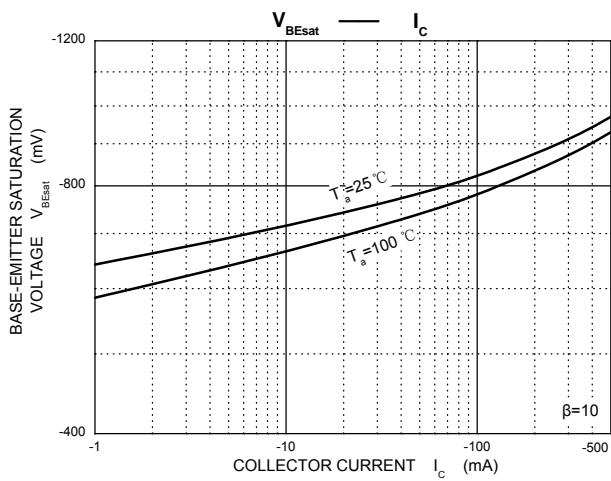
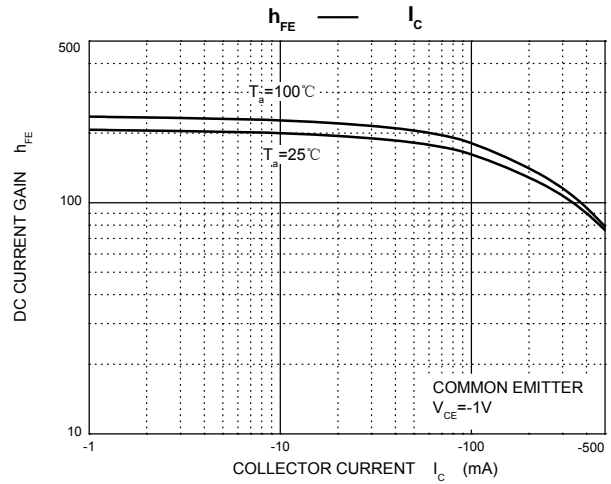
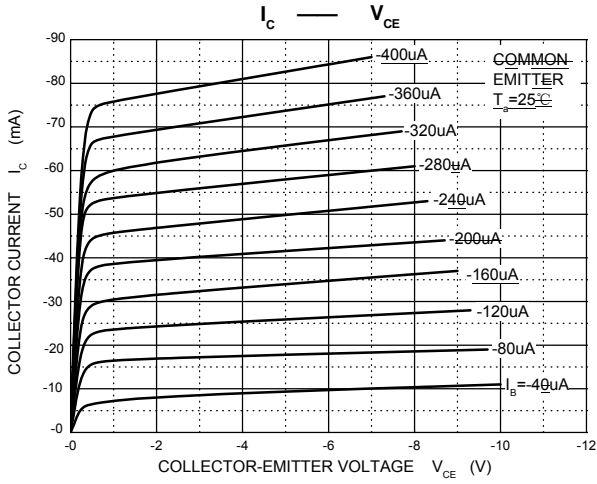
**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -40V, I_E = 0$		-0.1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE} = -20V, I_B = 0$		-0.1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -3V, I_C = 0$		-0.1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -50mA$	120	400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-1.2	V
Transition frequency	$f_T$	$V_{CE} = -6V, I_C = -20mA$ $f = 30MHz$	150		MHz

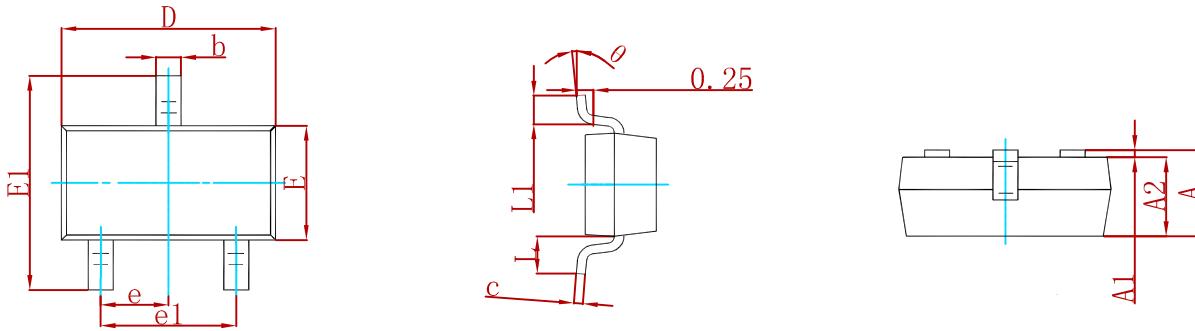
**CLASSIFICATION OF  $h_{FE(1)}$** 

Rank	L	H
Range	120-200	200-350

Typical Characteristics

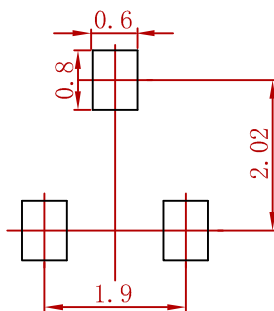


**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Suggested Pad Layout**



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance: ± 0.05mm.  
 3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
S8550-MS	SOT-23	3000

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